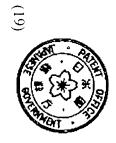
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(74) Representative:

(54) CONDUCTOR LAYER, CAPACITOR USING CONDUCTOR LAYER AND MANUFACTURE THEREOF

(57) Abstract:

PURPOSE: To obtain a conductor layer whose surface is flat, and a capacitor using said layer wherein electric field does not concentrate and dielectric strength is increased, by forming the conductor layer by using amorphous silicon containing no crystal grains.

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oxygen is used as reaction gas. Vapor composed of the amorphous silicon an insulating layer 7 is formed, it is region in contact with drain 4. After eliminated from the region except a method, an amorphous silicon layer 6 using the above manufacturing quality is formed on a substrate. By conductor layer composed of an of tetrasilane. Thus a flat surface trisilane, and 300-400°C in the case disilane, 350-450°C in the case of above gas, and its temperature is as growth is performed by heating the disilane or trisilane or tetrasilane and CONSTITUTION: Mixed gas of conducting layer 8 is formed. region except a region on the polycrystalline silicon layer is region on the amorphous layer 6. eliminated from the region except a MOS field effect transistor, and is subjected to vapor growth on a amorphous silicon layer of excellent follows; 400-500°C in the case of insulating layer 7, and a capacitor formed, it is eliminated from the After a conductor layer 8 like a layer 6, the insulating layer 7 and the

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